

Si3861DV

Integrated Load Switch

General Description

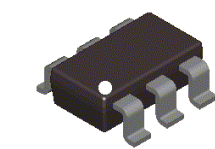
This device is particularly suited for compact power management in portable electronic equipment where 2.5V to 8V input and 2.8A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large P-Channel power MOSFET (Q2) in one tiny SuperSOT™-6 package.

Applications

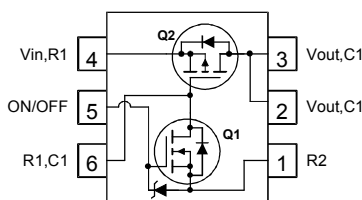
- Load switch
- Power management

Features

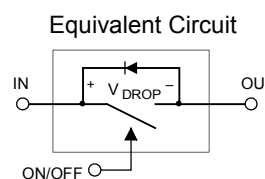
- -2.8 A, -8 V. $R_{DS(ON)} = 55\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
 $R_{DS(ON)} = 70\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$
 $R_{DS(ON)} = 100\text{ m}\Omega @ V_{GS} = -1.8\text{ V}$
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>6KV Human body model)
- High performance trench technology for extremely low $R_{DS(ON)}$



SuperSOT™-6



See Application Circuit



Absolute Maximum Ratings

$T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{IN}	Maximum Input Voltage	± 8	V
$V_{ON/OFF}$	High level ON/OFF voltage range	-0.5 to 8	V
I_{Load}	Load Current – Continuous (Note 1)	-2.8	A
	– Pulsed	-9	
P_D	Maximum Power Dissipation (Note 1)	0.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	180	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	60	$^\circ\text{C/W}$

Package Marking and Ordering Information

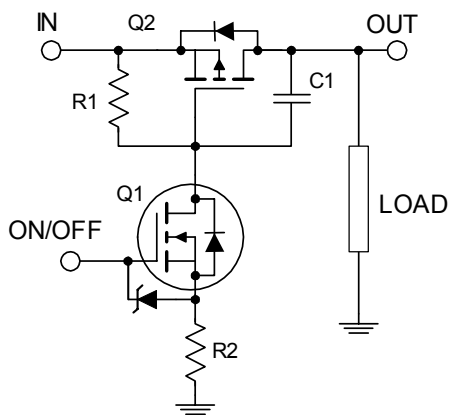
Device Marking	Device	Reel Size	Tape width	Quantity
.861	Si3861DV	7"	8mm	3000 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{IN}	Vin Breakdown Voltage	$V_{ON/OFF} = 0\text{ V}, I_D = -250\ \mu\text{A}$	8			V
I_{Load}	Zero Gate Voltage Drain Current	$V_{IN} = 6.4\text{ V}, V_{ON/OFF} = 0\text{ V}$			-1	μA
I_{FL}	Leakage Current, Forward	$V_{ON/OFF} = 0\text{ V}, V_{IN} = 8\text{ V}$			-100	nA
I_{RL}	Leakage Current, Reverse	$V_{ON/OFF} = 0\text{ V}, V_{IN} = -8\text{ V}$			100	nA
On Characteristics (Note 2)						
$V_{ON/OFF(th)}$	Gate Threshold Voltage	$V_{IN} = V_{ON/OFF}, I_D = -250\ \mu\text{A}$	0.4	0.9	1.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance (Q2)	$V_{IN} = 4.5\text{ V}, I_D = -2.8\text{ A}$		34	55	$\text{m}\Omega$
		$V_{IN} = 2.5\text{ V}, I_D = -2.5\text{ A}$		45	70	
		$V_{IN} = 1.8\text{ V}, I_D = -2.0\text{ A}$		64	100	
$R_{DS(on)}$	Static Drain-Source On-Resistance (Q1)	$V_{IN} = 4.5\text{ V}, I_D = 0.4\text{ A}$		3.1	4	Ω
		$V_{IN} = 2.7\text{ V}, I_D = 0.2\text{ A}$		3.8	5	
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current				-0.6	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{ON/OFF} = 0\text{ V}, I_S = -0.6\text{ A}$ (Note 2)			-1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
- Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

Si3861DV Load Switch Application Circuit**External Component Recommendation:**

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030.

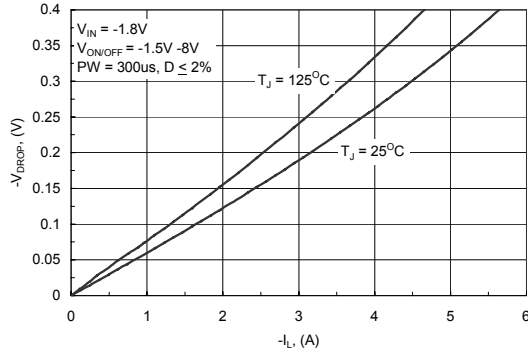


Figure 1. Conduction Voltage Drop Variation with Load Current.

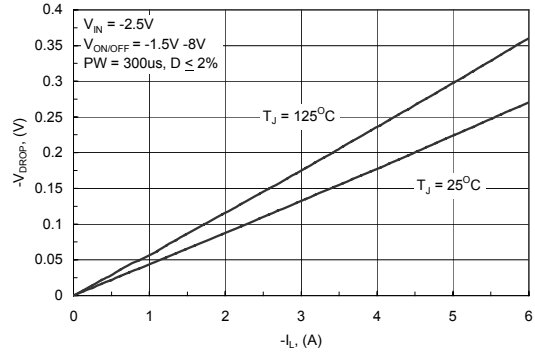


Figure 2. Conduction Voltage Drop Variation with Load Current.

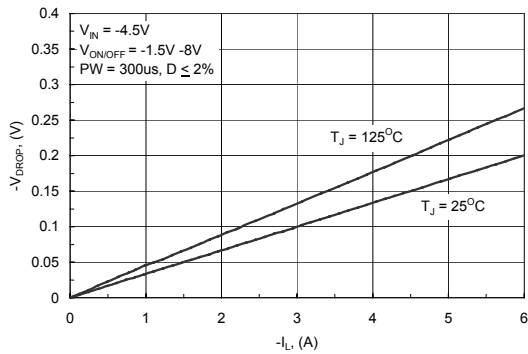


Figure 3. Conduction Voltage Drop Variation with Load Current.

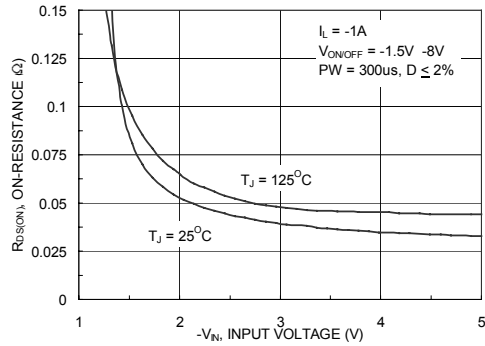
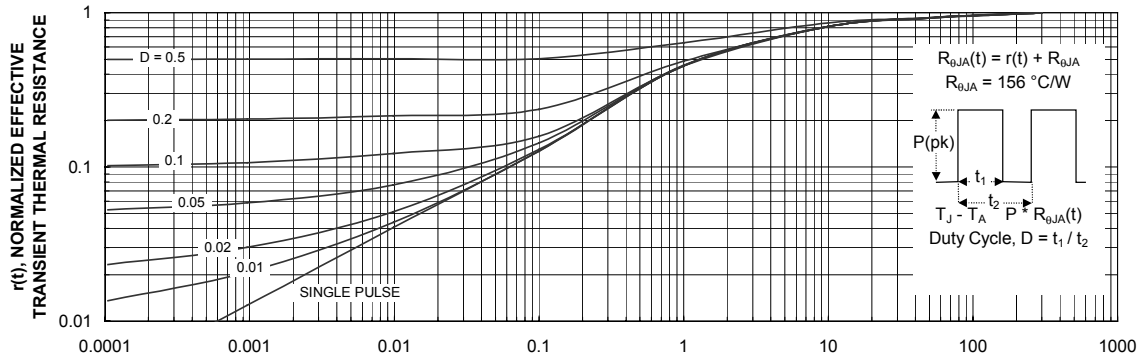


Figure 4. On-Resistance Variation With Input Voltage



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